

PRODUCT CHARACTERISTICS

VDSS	30V
$R_{DS(on)max}(V_{GS}=10\text{ V})$	10mΩ
$R_{DS(on)max}(V_{GS}=4.5\text{ V})$	13mΩ
ID	50A

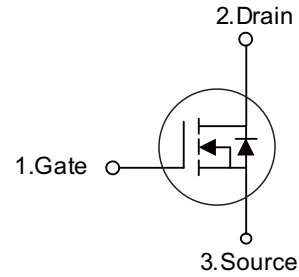
APPLICATIONS

- * Switching applications

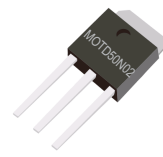
FEATURES

- * Low capacitance
- * Low gate charge
- * Fast switching capability
- * Avalanche energy specified

Symbol



TO-252



TO-251

ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT50N03D	TO-252	2500 pieces /Reel
N/A	MOT50N03C	TO-251	70 pieces/Tube

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	50	A
Pulsed Drain Current (Note 2)	I_{DM}	180	A
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	45	mJ
Power Dissipation	P_D	50	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 0.1\text{mH}$, $I_{AS} = 30\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$.

THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient (Note 3)	θ_{JA}	71.4	$^\circ\text{C/W}$
Junction to Case	θ_{JC}	3.0	$^\circ\text{C/W}$

Note: Surface-mounted on FR4 board using 1 sq in pad, 1 oz Cu



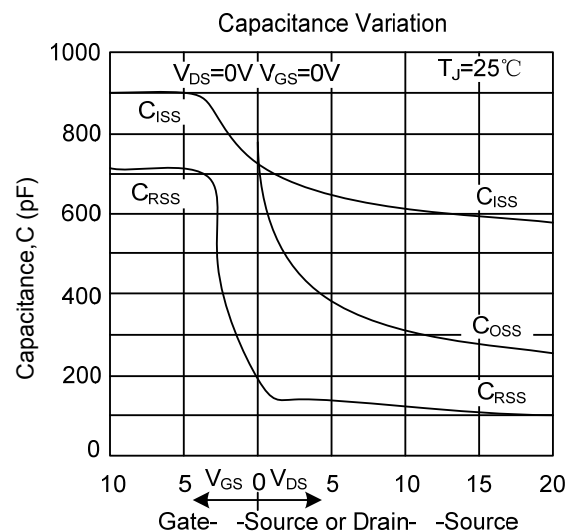
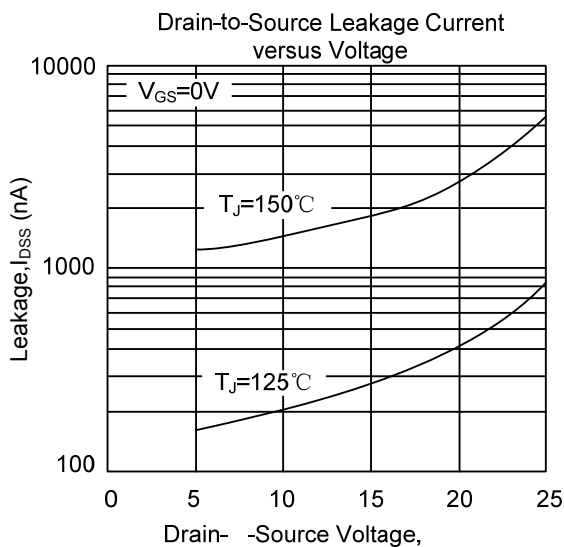
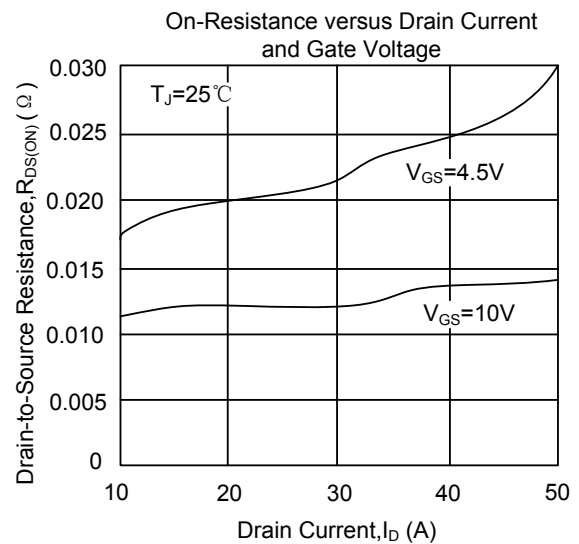
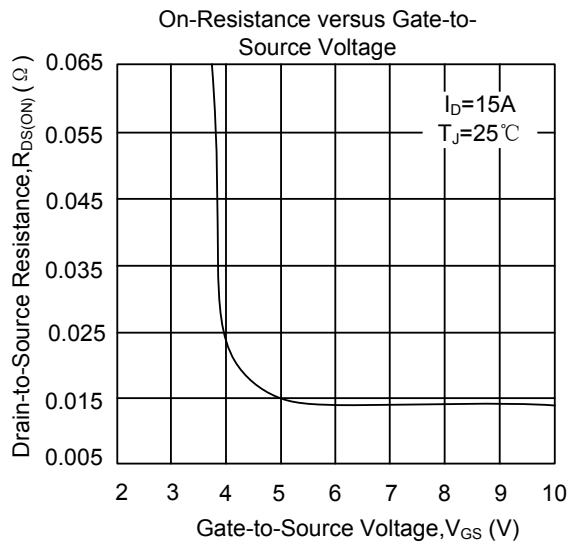
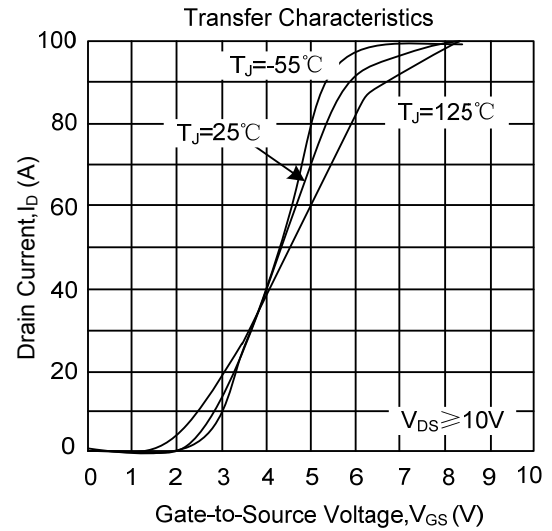
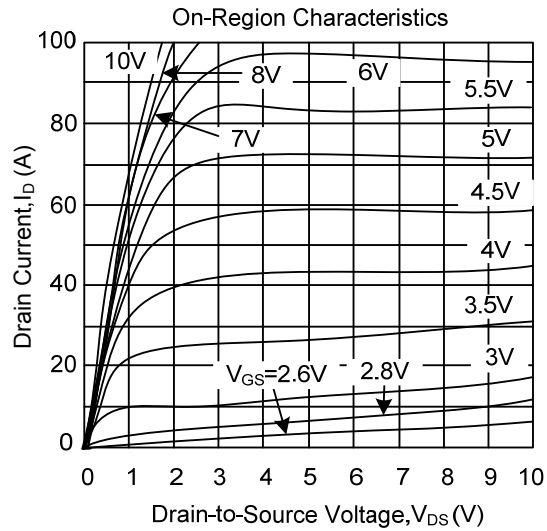
■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250 μA	30			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V			1.5	μA	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} = ±20V			±100	nA	
ON CHARACTERISTICS							
Gate-Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250 μA	1.0	1.7	2.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V	I _D = 15 A		8	10	mΩ
		V _{GS} = 4.5V	I _D = 10 A		10	13	mΩ
DYNAMIC PARAMETERS							
Input Capacitance	C _{ISS}	V _{DS} =12V, V _{GS} =0V, f=1MHz		610	750	pF	
Output Capacitance	C _{OSS}			300		pF	
Reverse Transfer Capacitance	C _{RSS}			125		pF	
SWITCHING PARAMETERS							
Turn-ON Delay Time	t _{D(ON)}	V _{GS} = 4.5 V, V _{DS} =15 V, I _D = 30 A, R _G = 3.0Ω		8.2		ns	
Turn-ON Rise Time	t _R			9.6		ns	
Turn-OFF Delay Time	t _{D(OFF)}			11.2		ns	
Turn-OFF Fall-Time	t _F	V _{GS} = 11.5 V, V _{DS} =15 V, I _D = 30 A, R _G = 3.0Ω		6.8		ns	
Turn-ON Delay Time	t _{D(ON)}			5.0		ns	
Turn-ON Rise Time	t _R			84		ns	
Turn-OFF Delay Time	t _{D(OFF)}			15		ns	
Turn-OFF Fall-Time	t _F			4.0		ns	
Total Gate Charge	Q _G	V _{DS} =15V,V _{GS} =4.5V, I _D =30 A		6.0	10	nC	
Gate-to-Source Charge	Q _{GS}			1.9		nC	
Gate-to-Drain Charge	Q _{GD}			3.7		nC	
Total Gate Charge	Q _G	V _{DS} =15V,V _{GS} =11.5V, I _D =30 A		15		nC	
Gate-to-Source Charge	Q _{GS}			1.9		nC	
Gate-to-Drain Charge	Q _{GD}			3.9		nC	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage	V _{SD}	I _S =30 A, V _{GS} =0V		0.85	1.1	V	
Maximum Continuous Drain-Source Diode Forward Current	I _S				45	A	
Reverse Recovery Time	t _{rr}	I _S = 30 A, V _{GS} = 0 V,		24		ns	
Reverse Recovery Charge	Q _{RR}	dI /dt = 100 A/μs		14		nC	

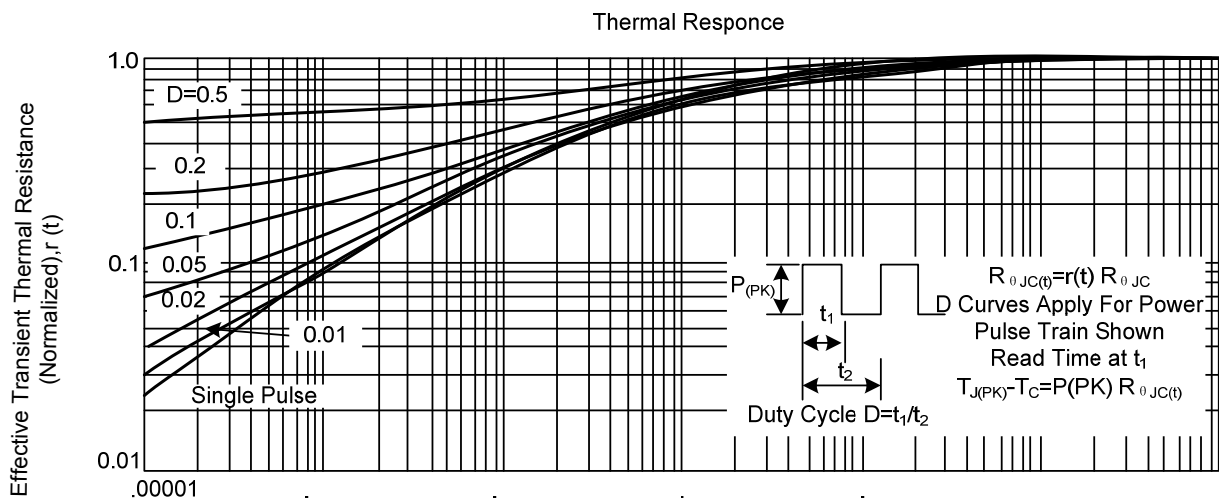
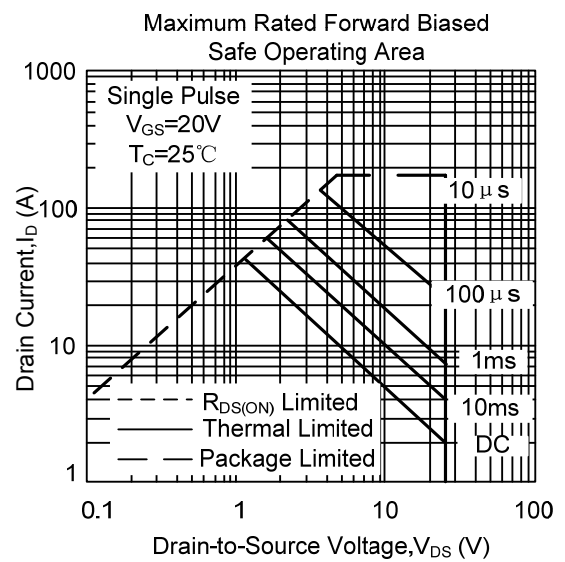
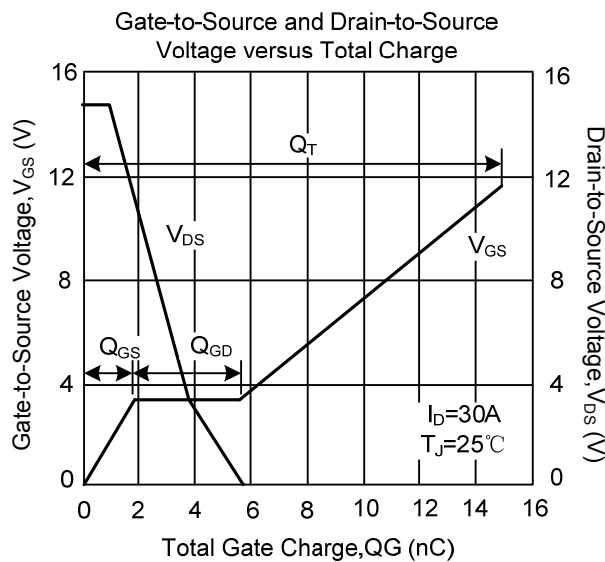
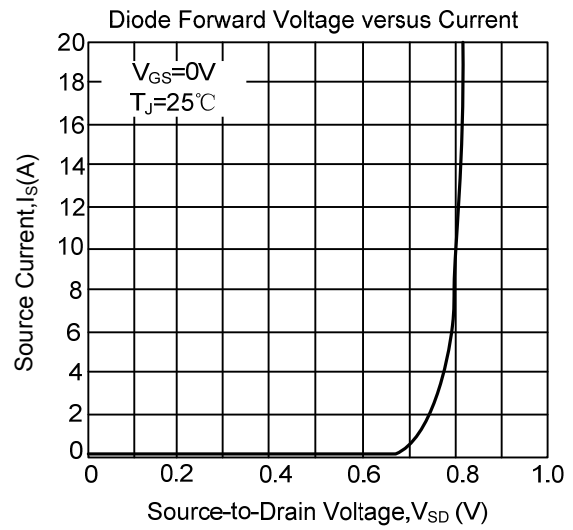
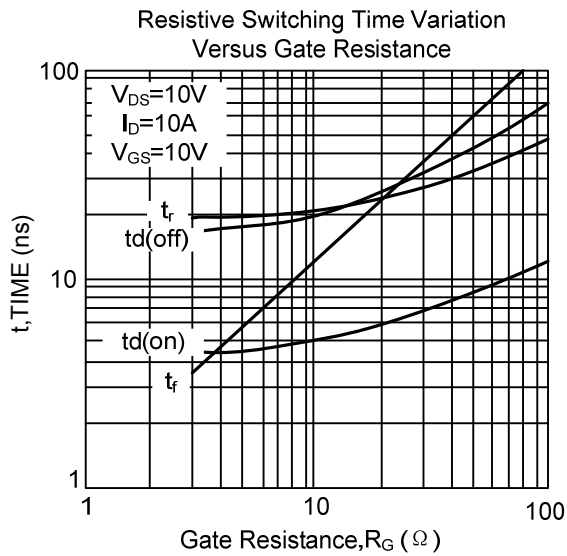
Notes: 1. Pulse width limited by $T_{J(MAX)}$

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$

■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ TO-251PACKAGE OUTLINE DIMENSIONS

